## MSKSEMI















**ESD** 

TVS

TSS

MOV

**GDT** 

**PLED** 

# Brodnet data speet

www.msksemi.com





- Extremely Fast Switching Speed
- Low forward voltage











**MARKING:** 

BAT54W	BAT54AW	BAT54CW	BAT54SW
KL5	KL6	KL7	KL8

## SOT-323

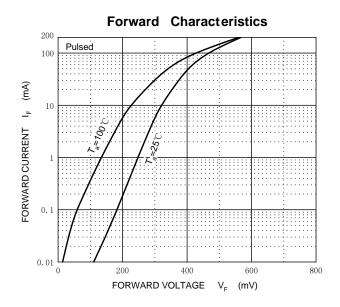
#### MAXIMUM RATINGS (T<sub>a</sub>=25℃ unless otherwise noted)

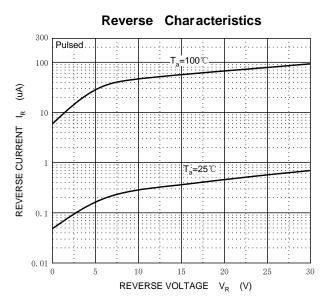
Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$		
Working Peak Reverse Voltage	$V_{RWM}$	30	V
DC Blocking Voltage	$V_{R}$		
Forward Continuous Current	I <sub>FM</sub>	200	mA
Non-repetitive Peak Forward Surge Current @t=8.3ms	I <sub>FSM</sub>	600	mA
Repetitive Peak Forward Current @ $t \le 1s$ , $\delta \le 0.5$	I <sub>FRM</sub>	300	mA
Power Dissipation	P <sub>D</sub>	200	mW
Thermal Resistance from Junction to Ambient	$R_{\Theta JA}$	500	°C/W
Operating Junction Temperature Range	Tj	-40 ~ +125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 ~ +150	°C

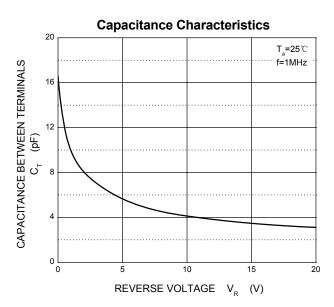
## **ELECTRICAL CHARACTERISTICS(Ta=25℃ unless otherwise specified)**

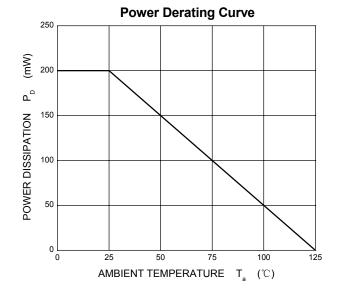
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	I <sub>R</sub> =100μA	30			V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =25V			2	μA
		I <sub>F1</sub> =0.1mA			0.24	V
		I <sub>F2</sub> =1mA			0.32	V
Forward voltage	$V_{F}$	I <sub>F3</sub> =10mA			0.40	V
		I <sub>F4</sub> =30mA			0.50	V
		I <sub>F5</sub> =100mA			1	V
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =1V, f=1MHz			10	pF
Reverse recovery time	t <sub>rr</sub>	IF=IR=10mA Irr=0.1×IR,RL=100 Ω			5	ns





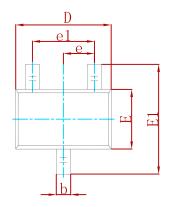


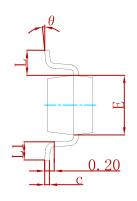


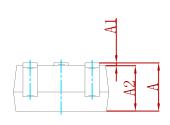




#### **PACKAGE MECHANICAL DATA**

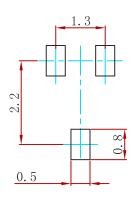






Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
Α	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
С	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
Е	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
е	0.650	) TYP	0.026	6 TYP
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021	REF
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

## **Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
BAT54AW	SOT-323	3000





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